

Features

- Silicon epitaxial planar transistors
- For switching and amplifier applications



1. Collector 2. Base 3. Emitter
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	45	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	800	mA
Peak Collector Current	$-I_{CM}$	1	A
Total Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$ at $-V_{CE} = 1\text{ V}$, $-I_C = 300\text{ mA}$	- RND BC337-16 h_{FE}	100	-	250	-
	- RND BC337-40 h_{FE}	250	-	630	-
	h_{FE}	60	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 45\text{ V}$	$-I_{CBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	50	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	45	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	-	0.7	V
Base Emitter On Voltage at $-V_{CE} = 1\text{ V}$, $-I_C = 300\text{ mA}$	$-V_{BE(on)}$	-	-	1.2	V
Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 50\text{ MHz}$	f_T	-	100	-	MHz
Collector Base Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cbo}	-	12	-	pF

